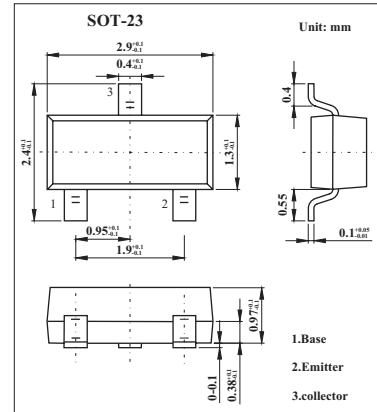


## PNP Transistors

## KST9015

## ■ Features

- Complementary to KST9014

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-50	V
Collector-Emitter Voltage	$V_{CE0}$	-45	V
Emitter-Base Voltage	$V_{EB0}$	-5	V
Collector Current -Continuous	$I_c$	-0.1	A
Collector Power Dissipation	$P_c$	0.2	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CB0}$	$I_c = -100\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{CE0}$	$I_c = -1\text{mA}, I_B = 0$	-45			V
Emitter-base Breakdown voltage	$V_{EB0}$	$I_E = -100\mu\text{A}, I_c = 0$	-5			V
Collector cutoff current	$I_{cBO}$	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_c = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -5\text{V}, I_c = -1\text{mA}$	200		1000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -100\text{mA}, I_B = -10\text{mA}$			-1	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_c = -10\text{mA}, f = 30\text{MHz}$	150			MHz

■  $h_{FE}$  Classification

Marking	M6	
Rank	L	H
$h_{FE}$	200 to 450	450 to 1000

# KST9015

■ Typical Characteristics

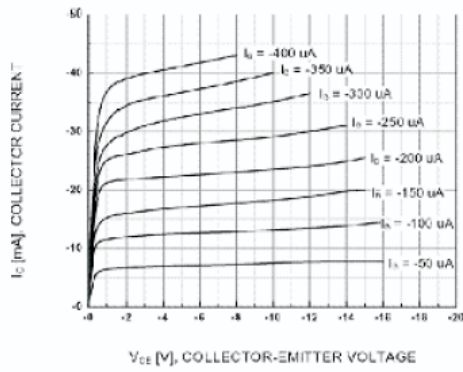


Figure 1. Static Characteristic

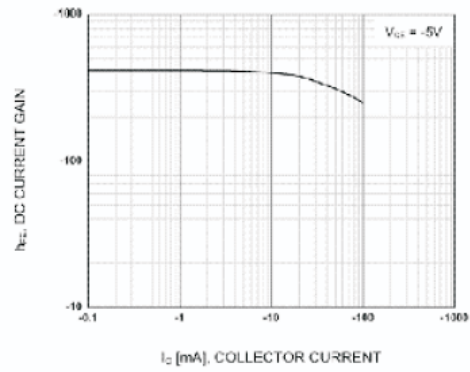


Figure 2. DC current Gain

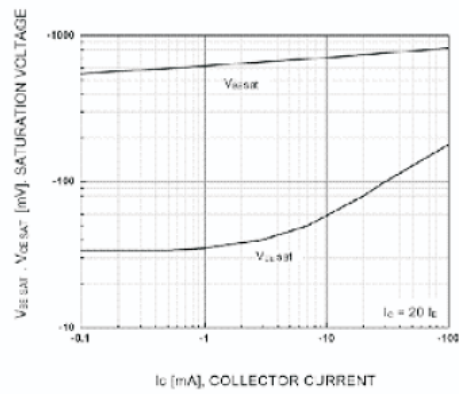


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

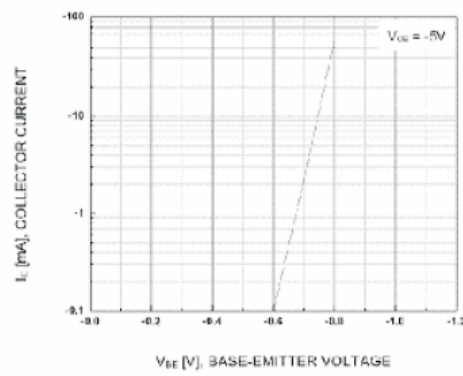


Figure 4. Base-Emitter On Voltage

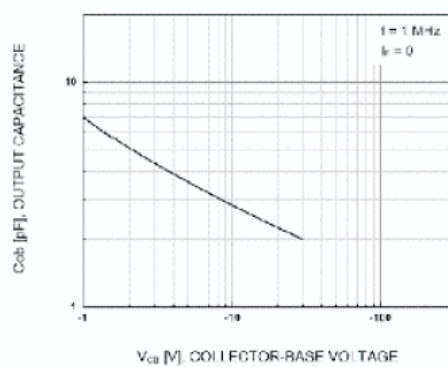


Figure 5. Collector Output Capacitance

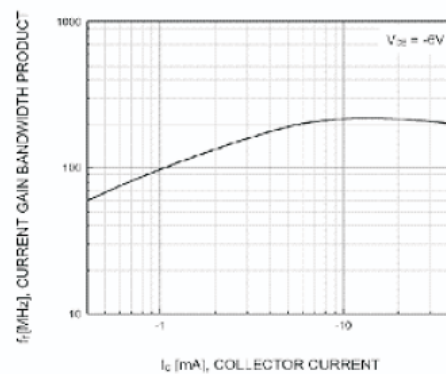


Figure 6. Current Gain Bandwidth Product